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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-WFQFN Exposed Pad
Supplier Device Package	48-HWQFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100ghana-w0

Email: info@E-XFL.COM

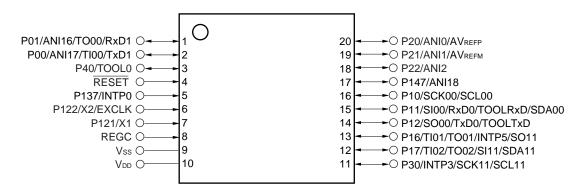
Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/G13 1. OUTLINE

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

• 20-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.

- **Notes 1.** Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

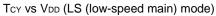
- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - **4.** When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

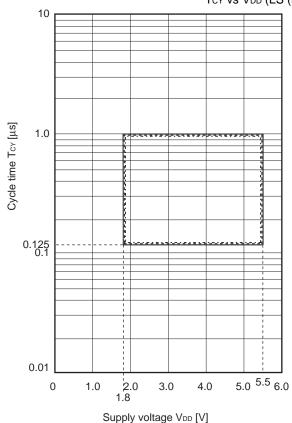
HS (high-speed main) mode: 2.7 V \leq Vpd \leq 5.5 V@1 MHz to 32 MHz

 $2.4~V \leq V_{DD} \leq 5.5~V@1~MHz$ to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 4 MHz

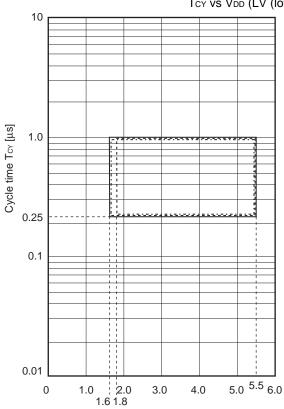
- **8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C





- When the high-speed on-chip oscillator clock is selected
- -- During self programming
- ___. When high-speed system clock is selected

Tcy vs Vdd (LV (low-voltage main) mode)



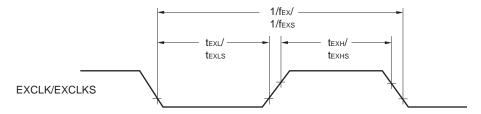
Supply voltage VDD [V]

- When the high-speed on-chip oscillator clock is selected During self programming
- --- When high-speed system clock is selected

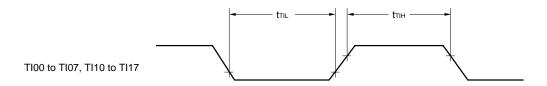
AC Timing Test Points

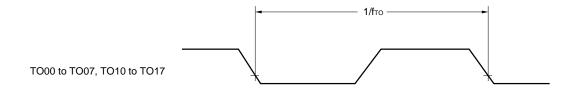


External System Clock Timing

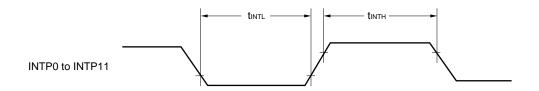


TI/TO Timing

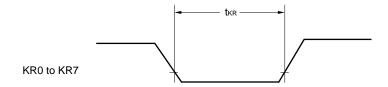




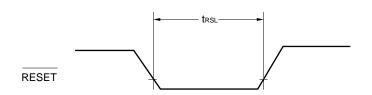
Interrupt Request Input Timing



Key Interrupt Input Timing



RESET Input Timing



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions I		` • .		`	LS (low-speed main) Mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t KCY1	tkcy1 ≥ 2/fclk	4.0 V ≤ EV _{DD0} ≤ 5.5 V	62.5		250		500		ns
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	83.3		250		500		ns
SCKp high-/low-level width	tкн1, tкL1			tксү1/2 — 7		tксү1/2 — 50		tксү1/2 — 50		ns
				tксү1/2 – 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑)	tsık1	4.0 V ≤ EV _{DI}	00 ≤ 5.5 V	23		110		110		ns
Note 1		2.7 V ≤ EV _D	00 ≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp [↑]) Note 2	tksı1	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF No.	ite 4		10		10		10	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remarks 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00))

(5) During communication at same potential (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	\ \	h-speed Mode	`	v-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	1/f _{MCK} + 85 Note2		1/fmck + 145 Note2		1/fмск + 145 Note2		ns
		$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1/f _{MCK} + 145 Note2		1/fmck + 145 Note2		1/f _{MCK} + 145 Note2		ns
		$1.8~V \leq EV_{DD0} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/f _{MCK} + 230 Note2		1/fmck + 230 Note2		1/fmck + 230 Note2		ns
		$1.7~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/f _{MCK} + 290 Note2		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
		$1.6~V \leq EV_{DD0} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	_		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V \leq EV _{DD0} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.7 V \leq EV _{DD0} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V \leq EV _{DD0} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ	_	_	0	405	0	405	ns

Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (Vpb tolerance (When 20- to 52-pin products)/EVpb tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	, 0	h-speed Mode	•	v-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	tsiĸ1	$\begin{array}{c} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array}$	44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, $	44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$	110		110		110		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
SIp hold time (from SCKp↓) Note 1	t KSI1	$\begin{array}{c} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \end{array}$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$\begin{array}{c} 2.7 \; \text{V} \leq \text{EV}_{\text{DD0}} < 4.0 \; \text{V}, \\ 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \end{array}$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array} $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
Delay time from SCKp↑ to	t KSO1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $		25		25		25	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ \begin{array}{c} 2.7 \; \text{V} \leq \text{EV}_{\text{DD0}} < 4.0 \; \text{V}, \\ 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \end{array} $		25		25		25	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$		25		25		25	ns
		$C_b=30~pF,~R_b=5.5~k\Omega$							

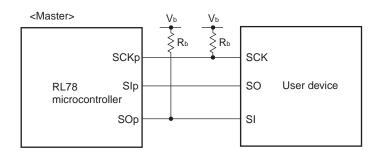
Notes

- 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** $R_b[\Omega]$:Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

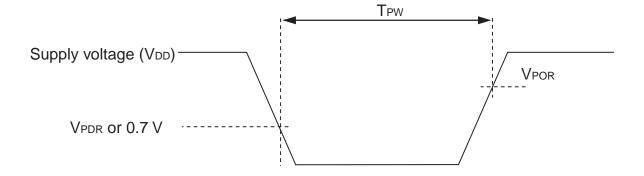
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, Ta = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	t AMP		5			μs

2.6.3 POR circuit characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	Power supply rise time	1.47	1.51	1.55	٧
	V _{PDR}	Power supply fall time	1.46	1.50	1.54	V
Minimum pulse width Note	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- 9. Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual Hardware.
- Remarks 1. fil.: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	250		ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tkcy1/2 - 24		ns
	t _{KL1}	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$		tkcy1/2 - 36		ns
		$2.4~V \leq EV_{DD0} \leq 5.5~V$		tксү1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsik1	4.0 V ≤ EV _{DD0} ≤ 5.5 V		66		ns
		2.7 V ≤ EV _{DD}	7 V ≤ EV _{DD0} ≤ 5.5 V			ns
		2.4 V ≤ EV _{DD}	₀ ≤ 5.5 V	113		ns
SIp hold time (from SCKp↑) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Not	te 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
 - g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 - n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0$ $V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$	600		ns
			$2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7$ V, $C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega$	1000		ns
			$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0$ V, $C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 5.5 \text{ k}\Omega$	2300		ns
SCKp high-level width			$v_{0} \le 5.5 \text{ V}, 2.7 \text{ V} \le V_{b} \le 4.0 \text{ V},$ $R_{b} = 1.4 \text{ k}\Omega$	tkcy1/2 - 150		ns
		2.7 V ≤ EV _{DD} C _b = 30 pF, F	$_{0}$ < 4.0 V, 2.3 V \leq V _b \leq 2.7 V, R_{b} = 2.7 k Ω	tkcy1/2 - 340		ns
		2.4 V ≤ EV _{DD} C _b = 30 pF, F	$_{0}$ < 3.3 V, 1.6 V \leq V _b \leq 2.0 V, $_{R_{b}}$ = 5.5 k $_{\Omega}$	tkcy1/2 - 916		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD} C _b = 30 pF, F	$_{0.0} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V},$ $R_{b} = 1.4 \text{ k}\Omega$	tkcy1/2 - 24		ns
		2.7 V ≤ EV _{DD} C _b = 30 pF, F	$_{0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $R_{b} = 2.7 \text{ k}\Omega$	tkcy1/2 - 36		ns
	_	2.4 V ≤ EV _{DD} C _b = 30 pF, F	$_{0} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$ $R_{\text{b}} = 5.5 \text{ k}\Omega$	tkcy1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	2.125		39	μs
		l-	$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	3.1875		39	μs
			$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution $EVDD0 \le AV_{REFP} = V_{DD}^{Notes 3}$,	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	E _F s	10-bit resolution EVDD0 \leq AV _{REFP} = V _{DD} Notes 3,	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±3.5	LSB
Differential linearity error	DLE	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI26		0		AV _{REFP} and EV _{DD0}	V

Notes 1. Excludes quantization error ($\pm 1/2$ LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%FSR$ to the MAX. value when AV_{REFP} = V_{DD}.

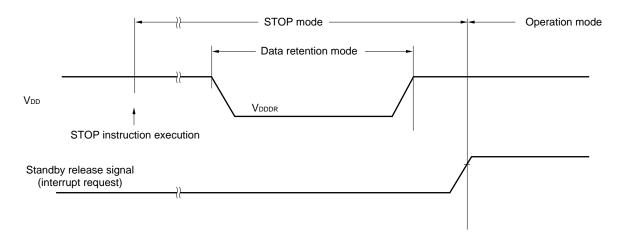
Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

3.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the data is retained before a POR reset is effected, but data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

(IX = 10 to 1100 e) 211 1 2 100 2 010 1)										
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit				
CPU/peripheral hardware clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V		1		32	MHz			
Number of code flash rewrites Notes 1,2,3	Cerwr	Retained for 20 years	Ta = 85°C	1,000			Times			
Number of data flash rewrites		Retained for 1 years	TA = 25°C		1,000,000					
Notes 1,2,3		Retained for 5 years	TA = 85°C	100,000						
		Retained for 20 years	TA = 85°C	10,000		·				

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library.
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.9 Dedicated Flash Memory Programmer Communication (UART)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

 $R5F100GAANA,\,R5F100GCANA,\,R5F100GDANA,\,R5F100GEANA,\,R5F100GFANA,\,R5F100GGANA,\,R5F100GCANA,\,R5F$

R5F100GHANA, R5F100GJANA, R5F100GKANA, R5F100GLANA

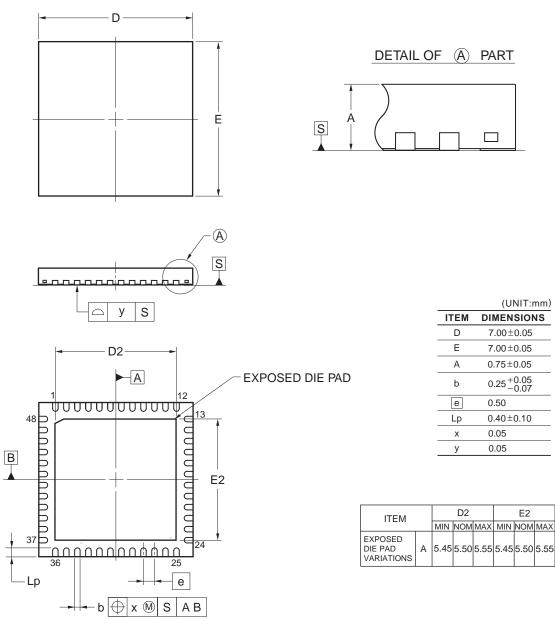
R5F101GAANA, R5F101GCANA, R5F101GDANA, R5F101GEANA, R5F101GFANA, R5F101GHANA, R5F101GHANA, R5F101GKANA, R5F10

R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA

R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA

R5F100GAGNA, R5F100GCGNA, R5F100GDGNA, R5F100GEGNA, R5F100GFGNA, R5F100GHGNA, R5F100GHGNA, R5F100GJGNA

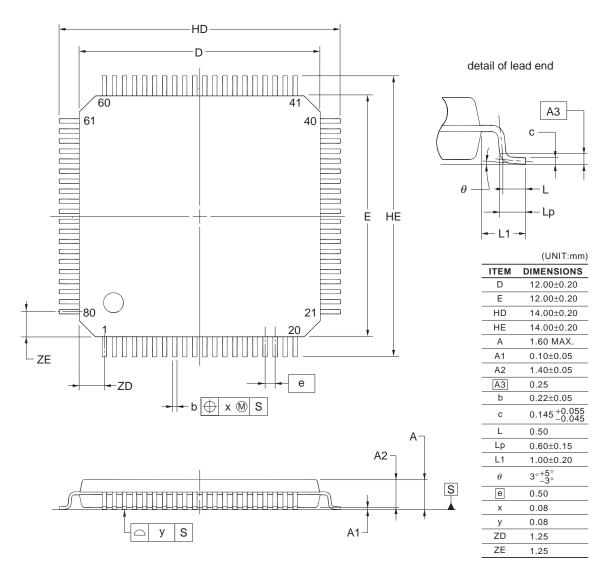
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	P48K8-50-5B4-4	0.13



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R5F100MFAFB, R5F100MGAFB, R5F100MHAFB, R5F100MJAFB, R5F100MKAFB, R5F100MLAFB R5F101MFAFB, R5F101MGAFB, R5F101MHAFB, R5F101MJAFB, R5F101MKAFB, R5F101MLAFB R5F100MFDFB, R5F100MGDFB, R5F100MHDFB, R5F100MJDFB, R5F100MKDFB, R5F100MLDFB R5F101MFDFB, R5F101MGDFB, R5F101MHDFB, R5F101MJDFB, R5F101MKDFB, R5F101MLDFB R5F100MFGFB, R5F100MGGFB, R5F100MHGFB, R5F100MJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53



NOTE

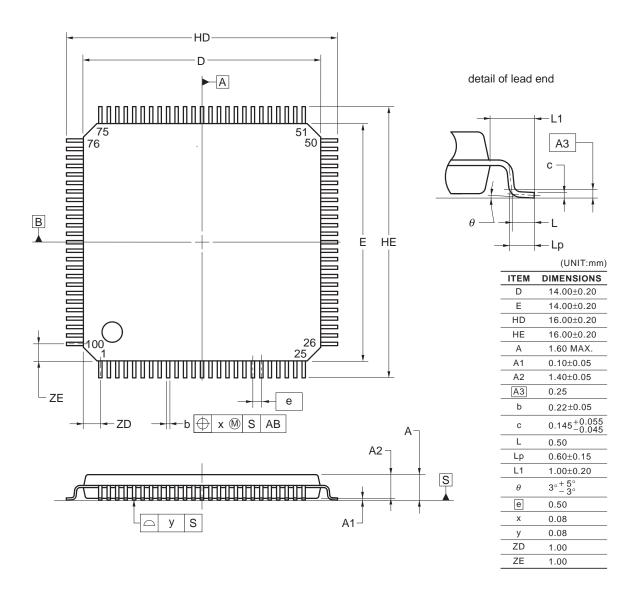
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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4.13 100-pin Products

R5F100PFAFB, R5F100PGAFB, R5F100PHAFB, R5F100PJAFB, R5F100PKAFB, R5F100PLAFB R5F101PFAFB, R5F101PGAFB, R5F101PHAFB, R5F101PJAFB, R5F101PKAFB, R5F101PLAFB R5F100PFDFB, R5F100PGDFB, R5F100PHDFB, R5F100PJDFB, R5F100PKDFB, R5F101PGDFB, R5F101PGDFB, R5F101PJDFB, R5F101PJDFB, R5F101PLDFB R5F100PFGFB, R5F100PGGFB, R5F100PHGFB, R5F100PJGFB

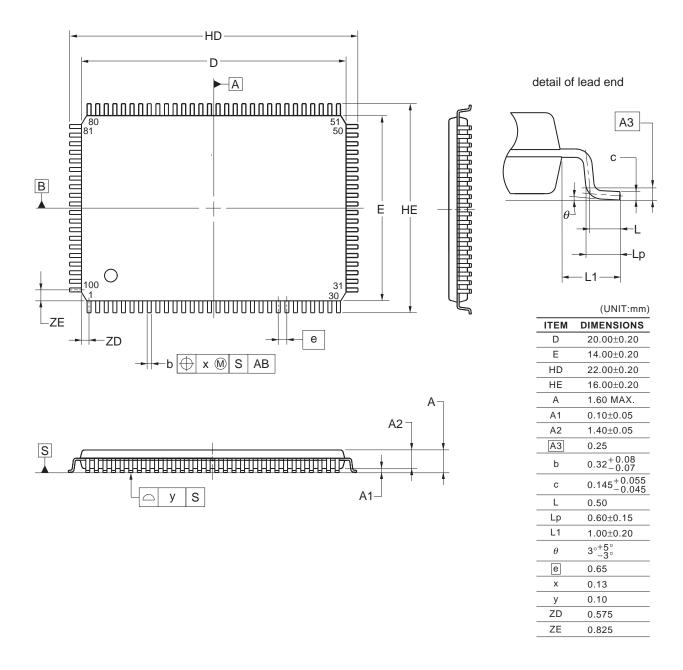
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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R5F100PFAFA, R5F100PGAFA, R5F100PHAFA, R5F100PJAFA, R5F100PKAFA, R5F100PLAFA R5F101PFAFA, R5F101PGAFA, R5F101PHAFA, R5F101PJAFA, R5F101PKAFA, R5F101PLAFA R5F100PFDFA, R5F100PGDFA, R5F100PHDFA, R5F100PJDFA, R5F100PKDFA, R5F101PLDFA R5F101PFDFA, R5F101PGDFA, R5F101PHDFA, R5F101PJDFA, R5F101PKDFA, R5F101PLDFA R5F100PFGFA, R5F100PGGFA, R5F100PHGFA, R5F100PJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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INCAISION I NSTOLA	Revision	History
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RL78/G13 Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Feb 29, 2012	-	First Edition issued	
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.	
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.	
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.	
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.	
		59, 63, 67	Descriptions of Note 8 in a table corrected.	
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.	
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.	
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.	
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.	
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.	
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.	
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.	
3.00	Aug 02, 2013	1	Modification of 1.1 Features	
		3	Modification of 1.2 List of Part Numbers	
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution	
		16 to 32	Modification of package type in 1.3.1 to 1.3.14	
		33	Modification of description in 1.4 Pin Identification	
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions	
		55	Modification of description in table of Absolute Maximum Ratings (T _A = 25°C)	
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics	
		57	Modification of table in 2.2.2 On-chip oscillator characteristics	
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics	
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics	
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100- pin products	
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products	
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products	
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products	
		75	Modification of (4) Peripheral Functions (Common to all products)	
		77	Modification of table in 2.4 AC Characteristics	
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation	
		80	Modification of figures of AC Timing Test Points and External System Clock Timing	